

1200V Trench and Fieldstop IGBT

PRODUCT SUMMARY		
V _{CE} (V)	1200	
I _C (A)	100 (T _C =25 °C)	50 (T _C =100 °C)
V _{CE(sat)} (V)	1.7	
I _{CM} (A)	150	

FEATURES

- Very Low V_{CEsat}
- Low turn-off losses
- High speed switching
- Maximum junction temperature 175°C
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)



RoHS
COMPLIANT
HALOGEN
FREE

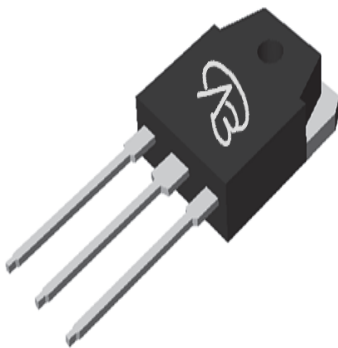
APPLICATIONS

- Telecommunications
 - Server and telecom power supplies
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Consumer and computing
 - ATX power supplies
- Industrial
 - Welding
 - Battery chargers
- Renewable energy
 - Solar (PV inverters)
- Switch mode power supplies (SMPS)

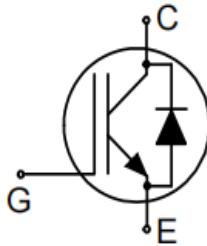
Package pin definition

- Pin1 G - Gate
- Pin2 C & backside - Collector
- Pin3 E - Emitter

TO-3P



Top View



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Collector-Emitter Voltage		V _{CE}	1200	V
Gate-Emitter Voltage		V _{GE}	±30	
Continuous Collector Current (T _J = 150 °C)	V _{GE} at 15 V	I _C	T _C = 25 °C	100
			T _C = 100 °C	50
Pulsed Collector Current ^a		I _{CM}	150	A
Diode Forward Current ^b		I _F	50	A
Maximum Power Dissipation		P _D	T _C = 25 °C	800
			T _C = 100 °C	400
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C
Short Circuit Withstand Time ^{TC=150}	V _{GE} = 15V, V _{CE} 400V	t _{sc}	3	μs
Short Circuit Withstand Time ^{TC=100}	V _{GE} = 15V, V _{CE} 330V		5	
Soldering Recommendations (Peak Temperature) ^c	for 10 s		260	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- Current limited by maximum junction temperature.
- 1.6 mm from case.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Maximum Junction-to-Case	R_{thJC}	-	0.17	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Collector-Emitter Breakdown Voltage	BV_{CE}	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$ $V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$		1200 1200	- -	- -	V
Gate-Source Threshold Voltage (N)	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_D = 250\text{ }\mu\text{A}$		4	5	6	V
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_J = 25\text{ }^\circ\text{C}$		-	1	20	μA
		$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$		-	1000	-	μA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE} = 0\text{ V}, V_{GS} = \pm 2.0\text{ V}$		-	-	100	nA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15\text{ V}$	$I_C = 50\text{ A}$	-	1.8	2.1	V
Forward Transconductance	g_{fs}	$V_{CE} = 20\text{ V}, I_C = 50\text{ A}$		-	40	-	S
Dynamic							
Input Capacitance	C_{ies}	$V_{GE} = 0\text{ V}, V_{CE} = 25\text{ V},$ $f = 500\text{ KHz}$		-	6300	-	pF
Output Capacitance	C_{oes}			-	210	-	
Reverse Transfer Capacitance	C_{res}			-	58	-	
Turn-on Energy	E_{on}	$V_{CE} = 400\text{ V}, V_{GE} = 0/15\text{V},$ $I_C = 50\text{ A}, R_g = 10\Omega$		-	0.41	-	nJ
Turn-off Energy	E_{off}			-	0.24	-	
Total Gate Charge	Q_g	$V_{GE} = 15\text{ V}$	$I_C = 50\text{ A}, V_{CE} = 400\text{ V}$	-	130	-	nC
Gate-Emitter Charge	Q_{ge}			-	14	-	
Gate to Collector Charge	Q_{gc}			-	31	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 400\text{ V}, V_{GE} = 0/15\text{V},$ $I_C = 50\text{ A}, R_g = 10\Omega$		-	46	-	ns
Rise Time	t_r			-	41	-	
Turn-Off Delay Time	$t_{d(off)}$			-	167	-	
Fall Time	t_f			-	36	-	
Internal emitter inductance measured 5 mm	L_E			-	13	-	
Diode Characteristics							
Diode Forward Current	I_F	IGBT symbol showing the integral reverse junction diode		-	-	50	A
Pulsed Diode Forward Current	I_{FM}			-	-	150	
Diode Forward Voltage	V_F	$I_F = 50\text{ A}$		-	1.85	2.0	V
Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 50\text{ A},$ $dI_F/dt = 200\text{ A}/\mu\text{s}, V_R = 400\text{ V}$		-	63	-	ns
Reverse Recovery Charge	Q_{rr}			-	0.3	-	μC
Reverse Recovery Current	I_{RRM}			-	11	-	A

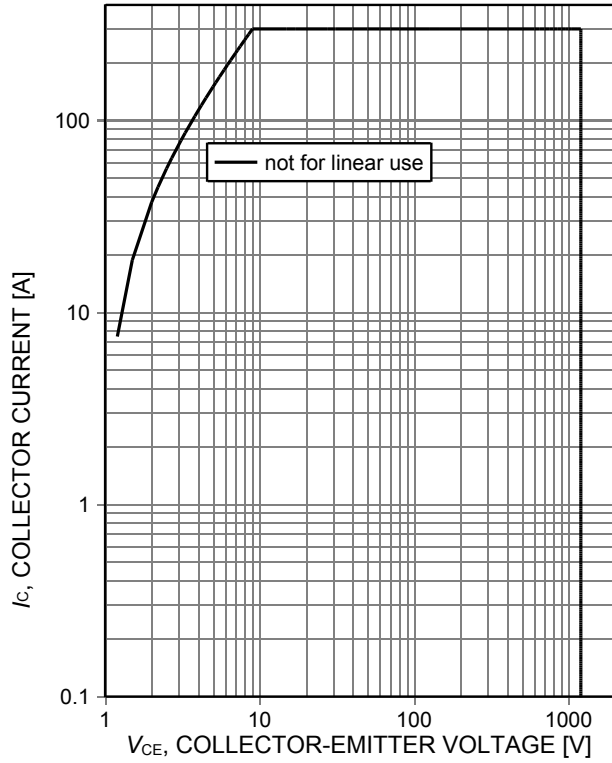


Figure 1. Forward bias safe operating area

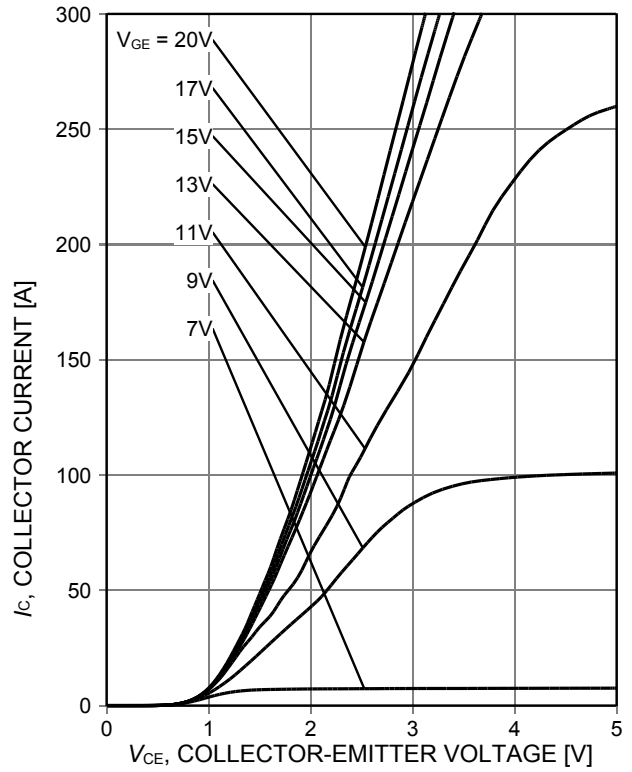


Figure 2. Typical output characteristic

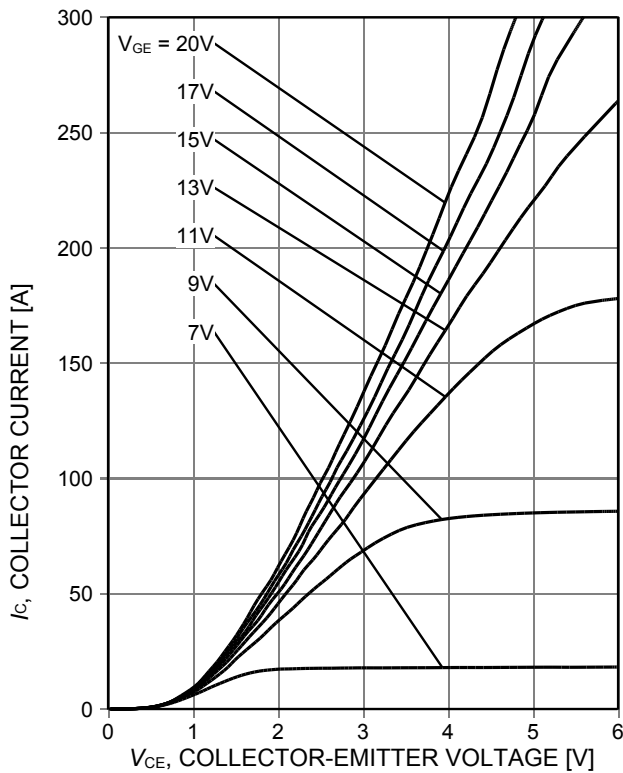


Figure 3. Typical output characteristic

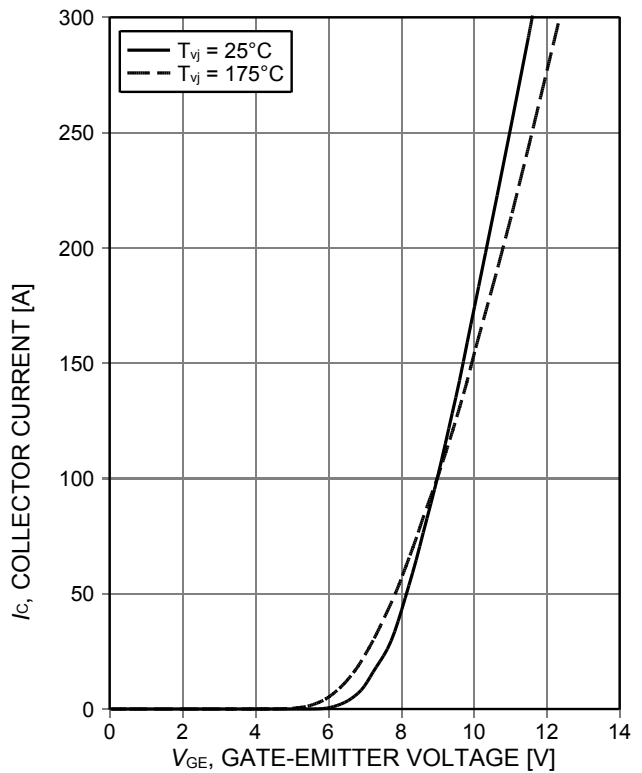


Figure 4. Typical transfer characteristic

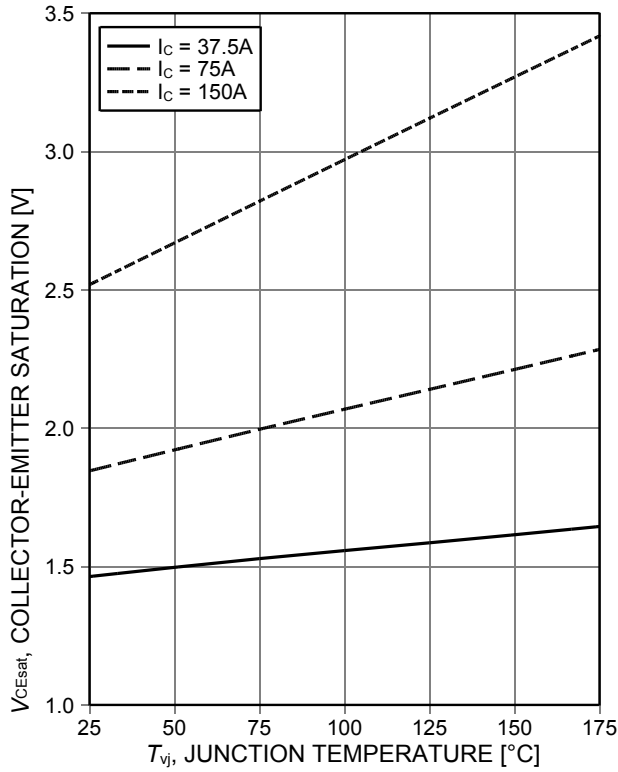


Figure 5. Typical collector-emitter saturation voltage as a function of junction temperature

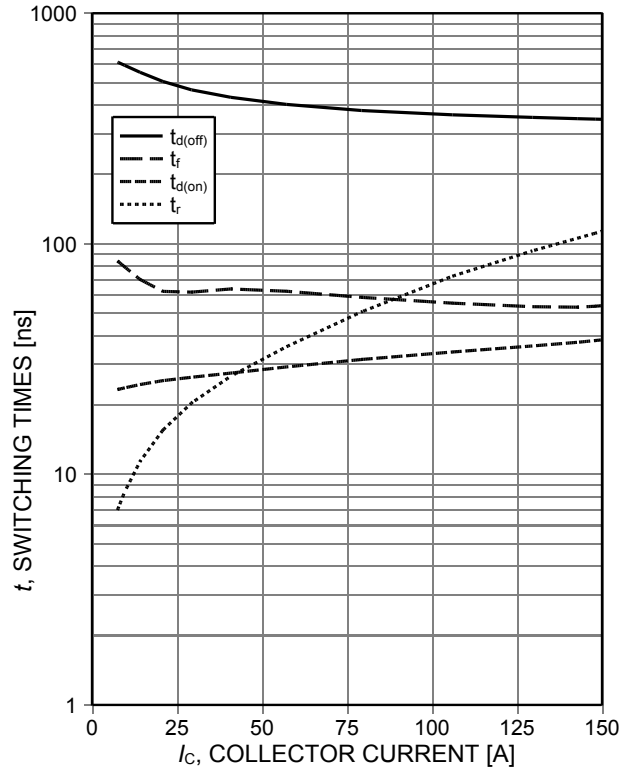


Figure 6. Typical switching times as a function of collector current

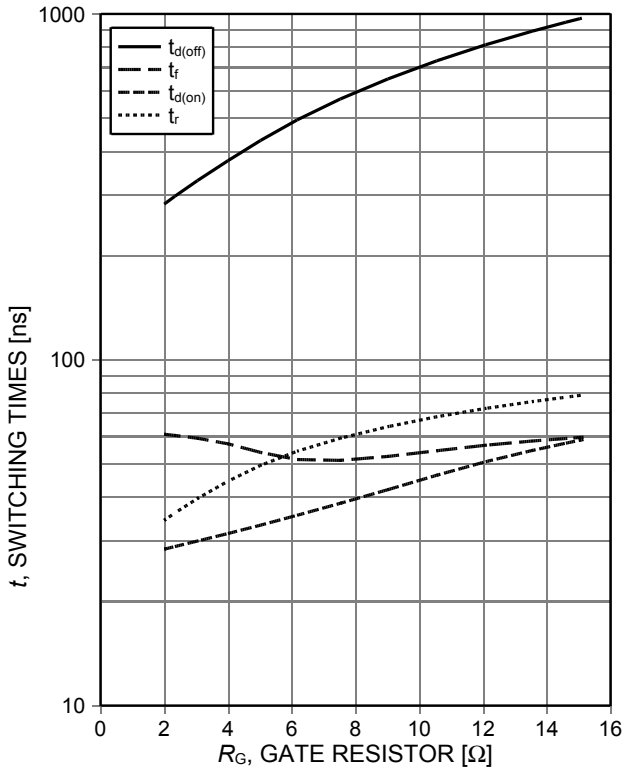


Figure 7. Typical switching times as a function of gate resistor

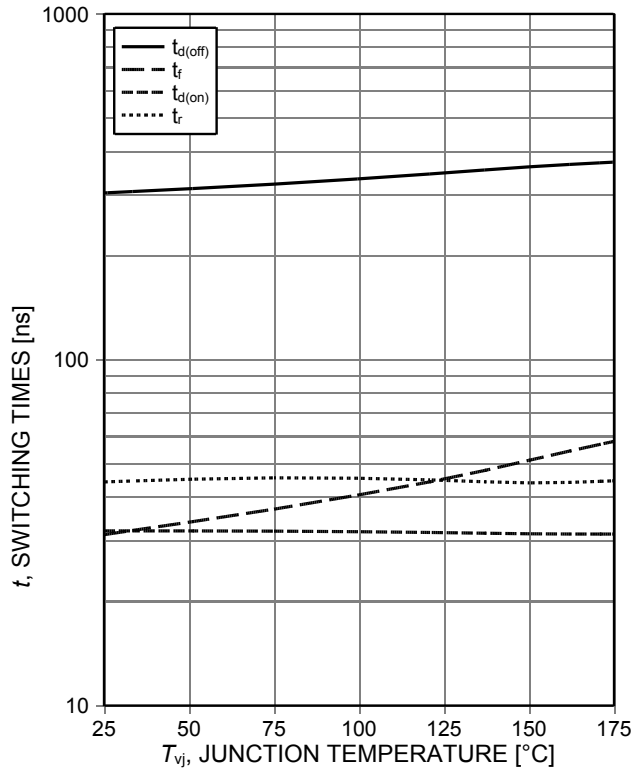


Figure 8. Typical switching times as a function of junction temperature

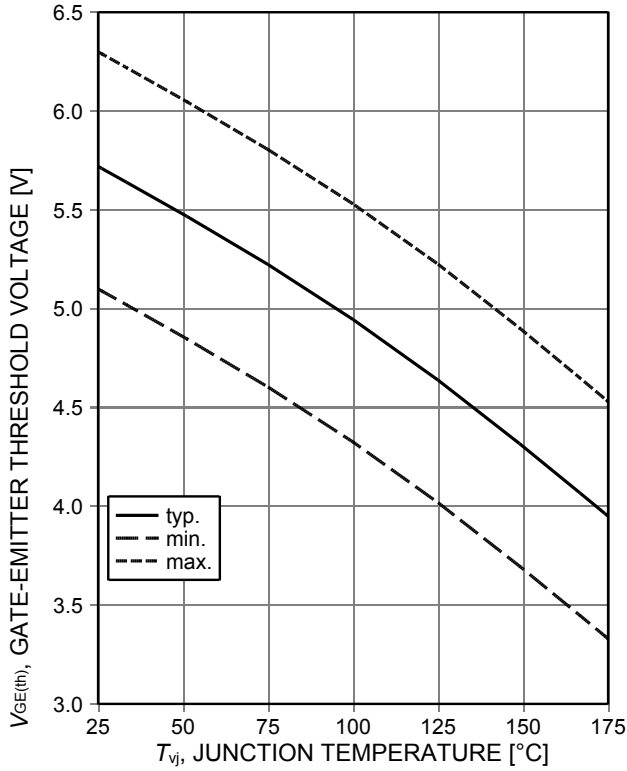


Figure 9. Gate-emitter threshold voltage as a function of junction temperature

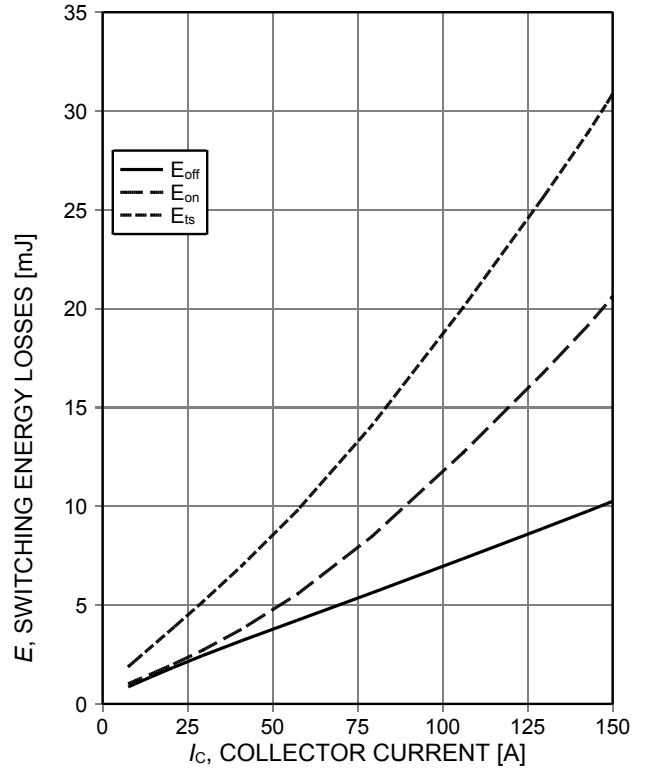


Figure 10. Typical switching energy losses as a function of collector current

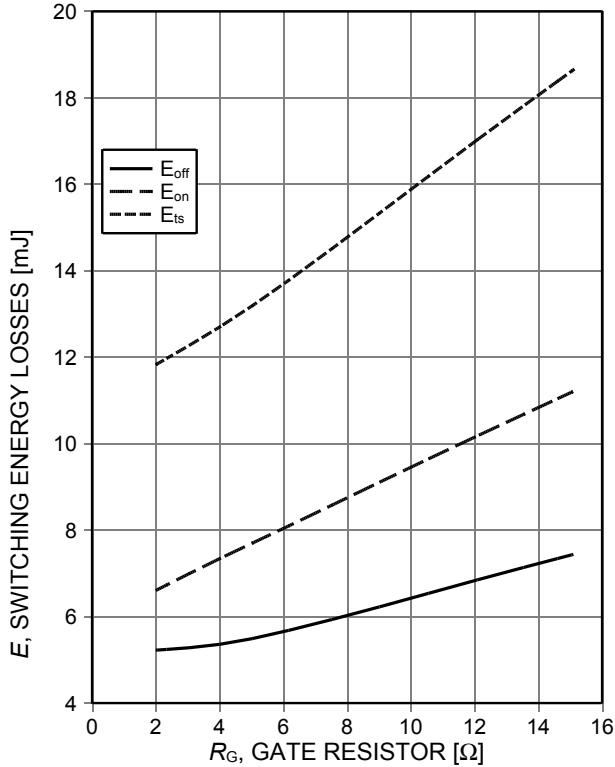


Figure 11. Typical switching energy losses as a function of gate resistor

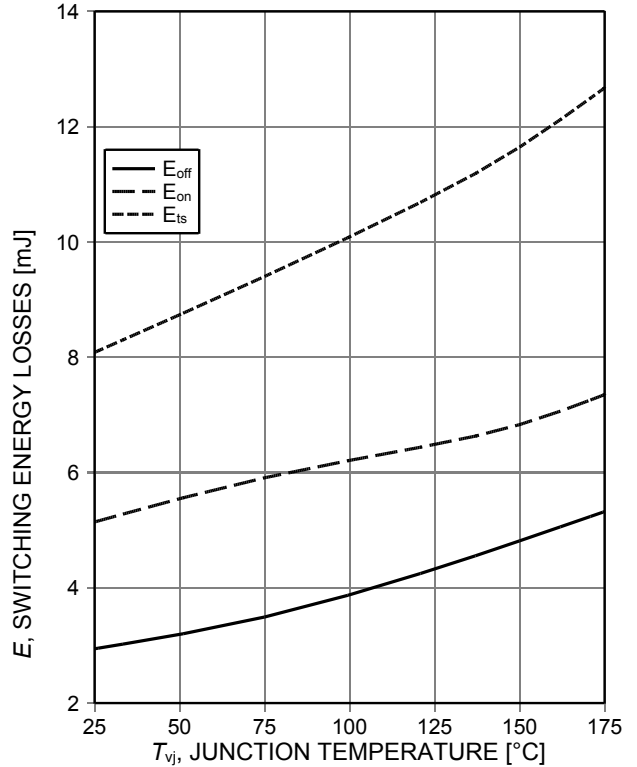


Figure 12. Typical switching energy losses as a function of junction temperature

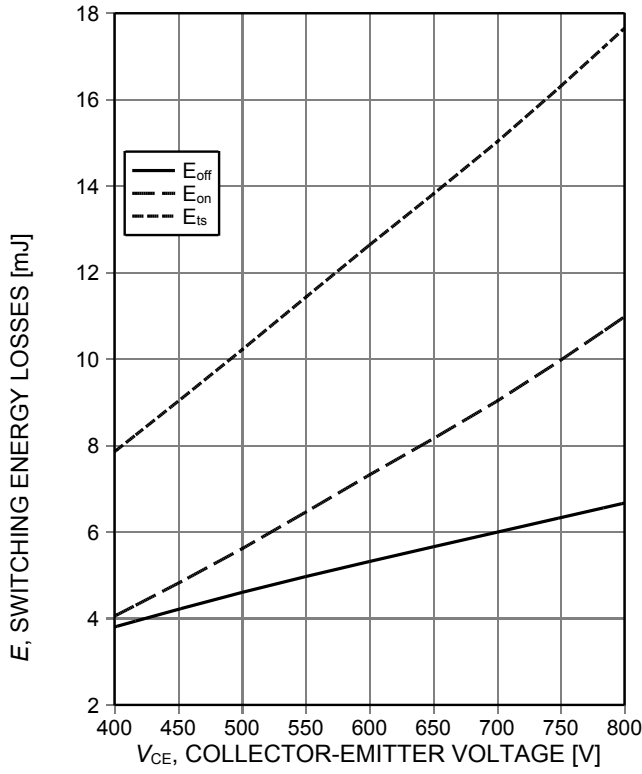


Figure 13. Typical switching energy losses as a function of collector emitter voltage

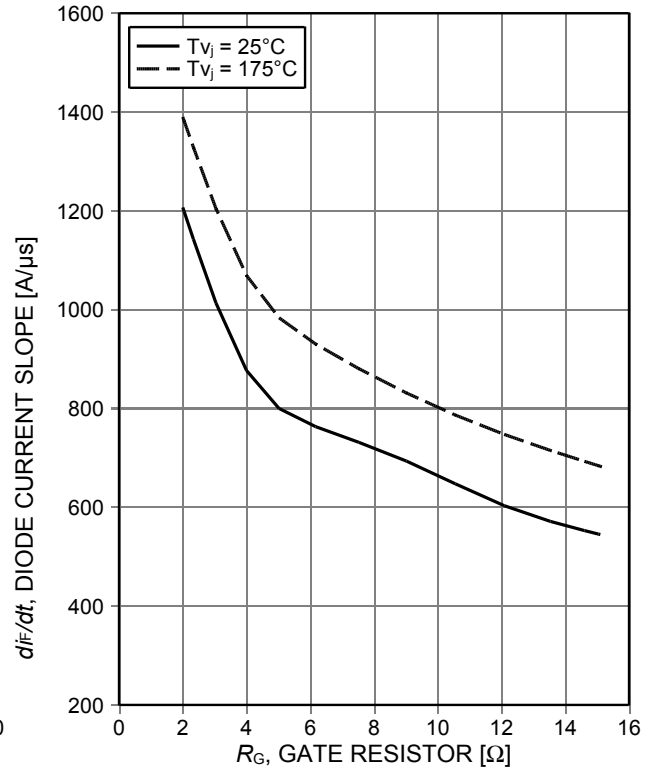


Figure 14. Typical diode current slope as a function of gate resistor

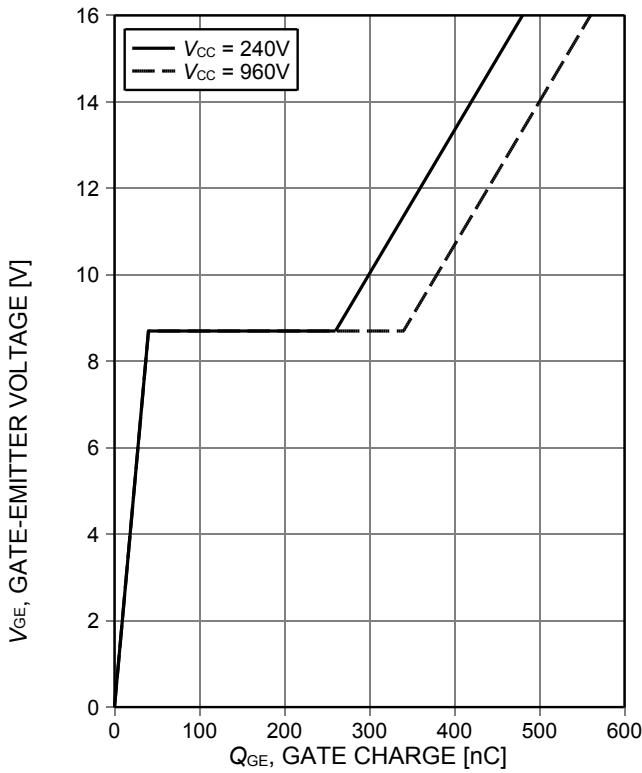


Figure 15. Typical gate charge

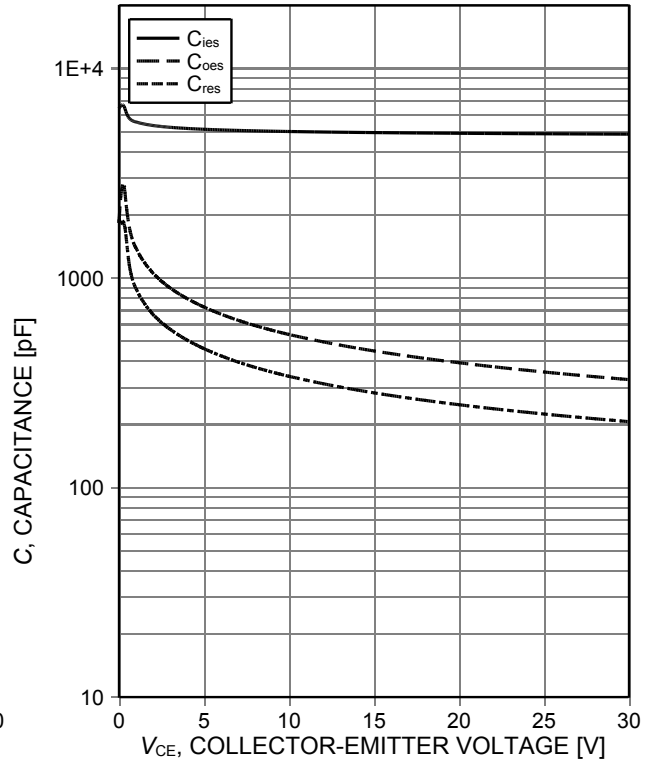


Figure 16. Typical capacitance as a function of collector-emitter voltage

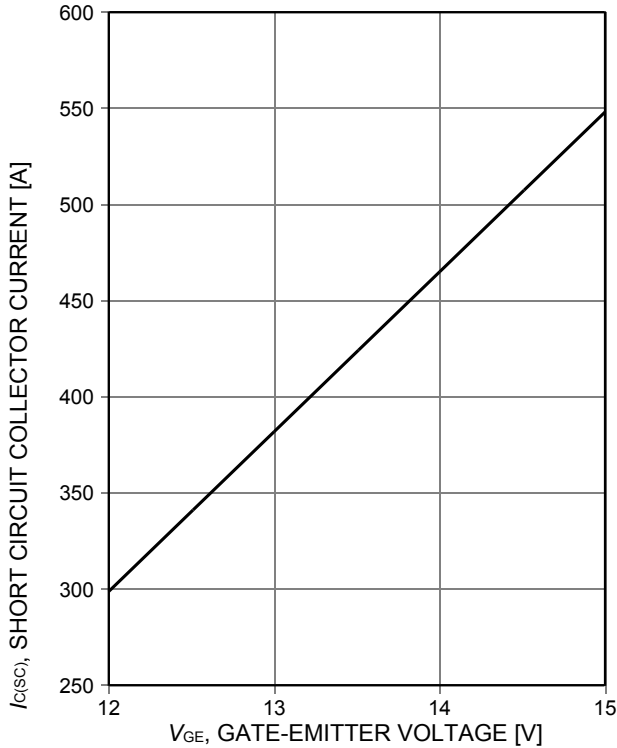


Figure 17. Typical short circuit collector current as a function of gate-emitter voltage

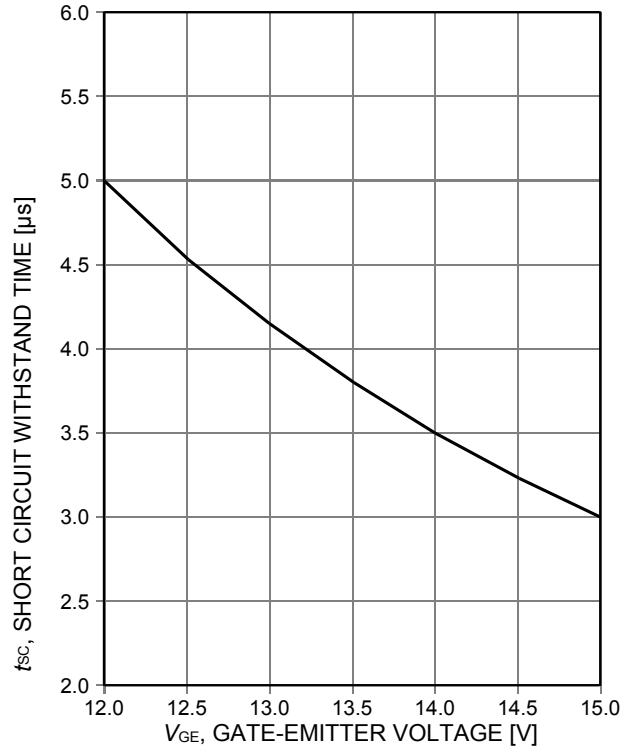


Figure 18. Short circuit withstand time as a function of gate-emitter voltage

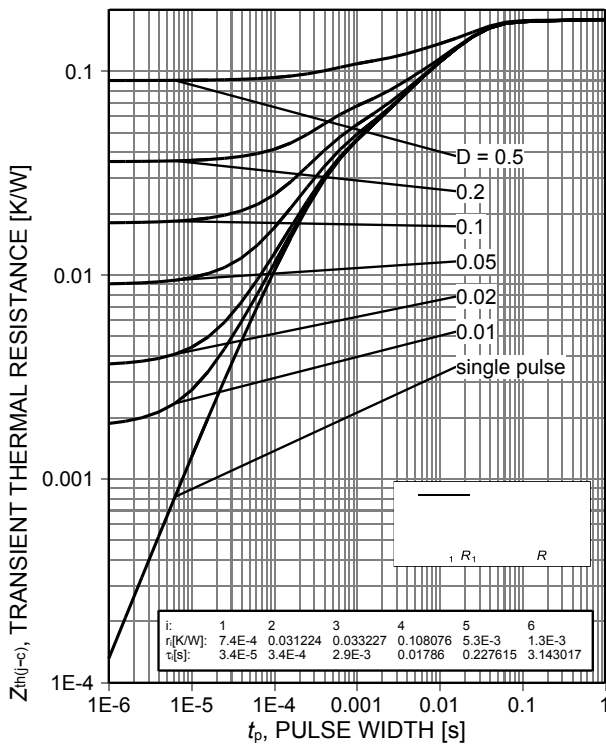


Figure 19. IGBT transient thermal resistance

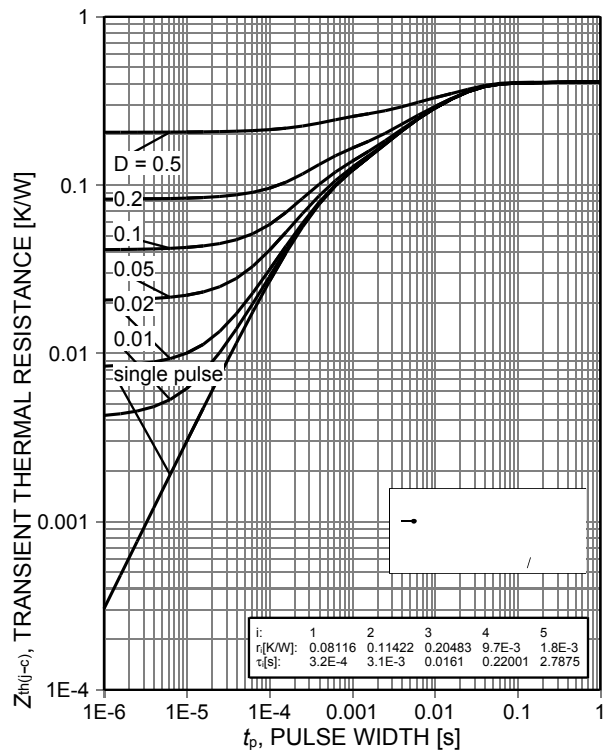


Figure 20. Diode transient thermal impedance as a function of pulse width

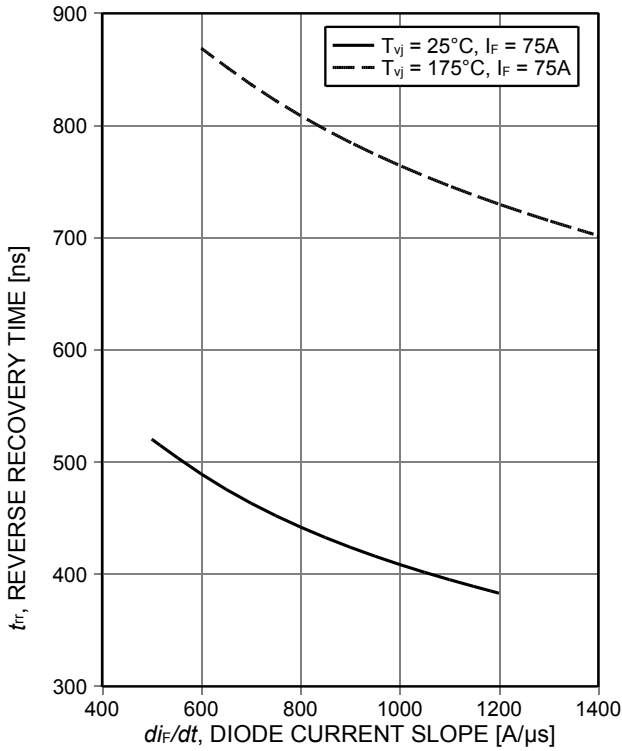


Figure 21. Typical reverse recovery time as a function of diode current slope

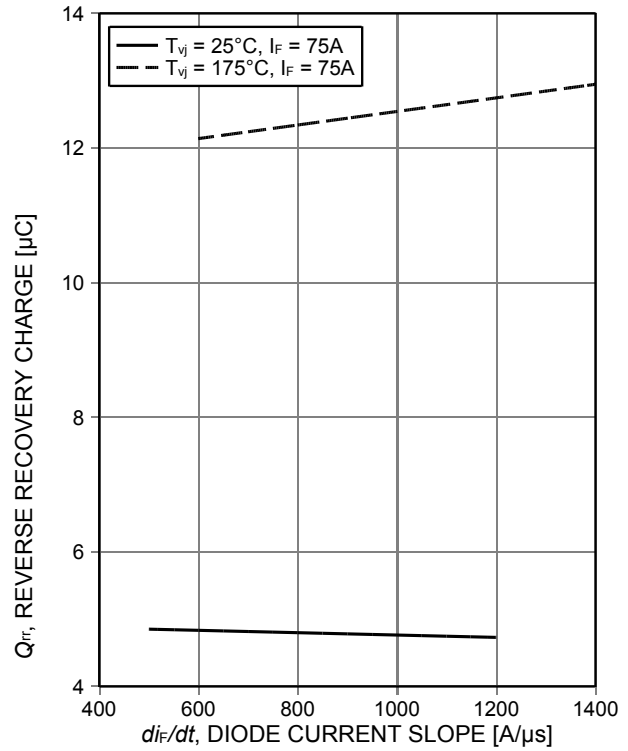


Figure 22. Typical reverse recovery charge as a function of diode current slope

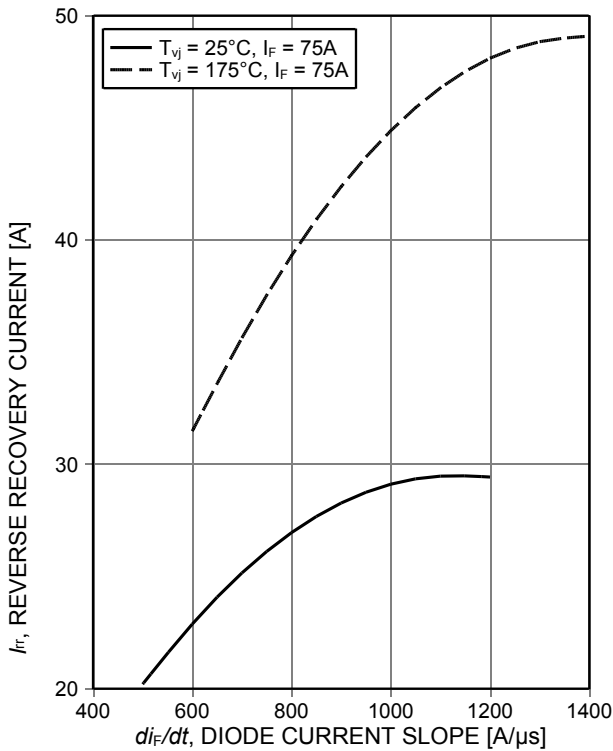


Figure 23. Typical reverse recovery current as a function of diode current slope

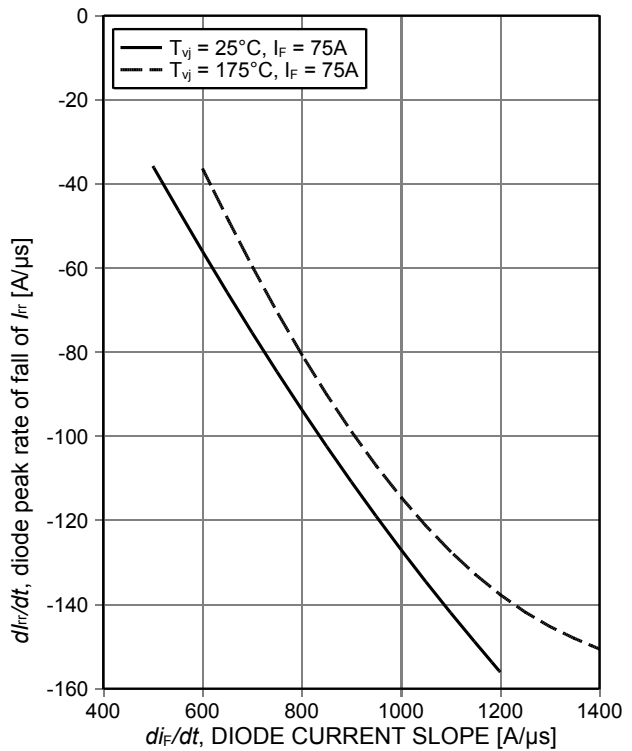


Figure 24. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope

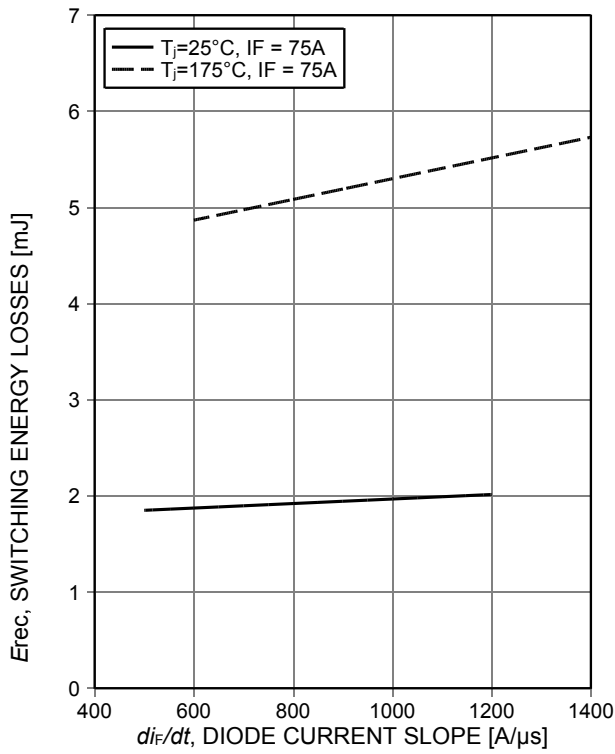


Figure 25. Typical reverse energy losses as a function of diode current slope

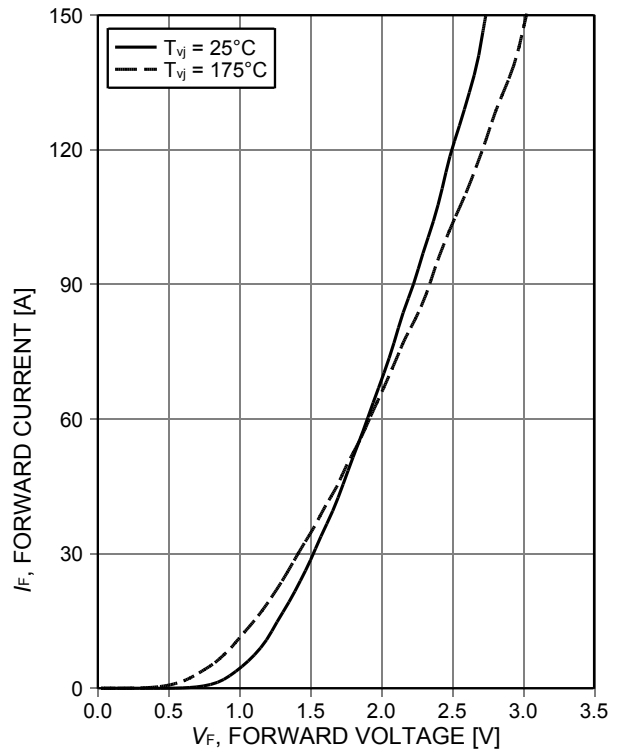


Figure 26. Typical diode forward current as a function of forward voltage

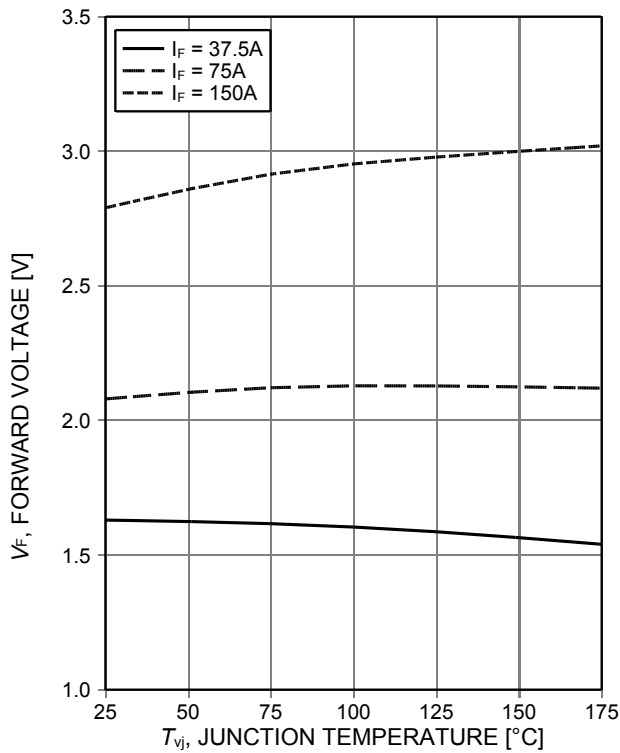
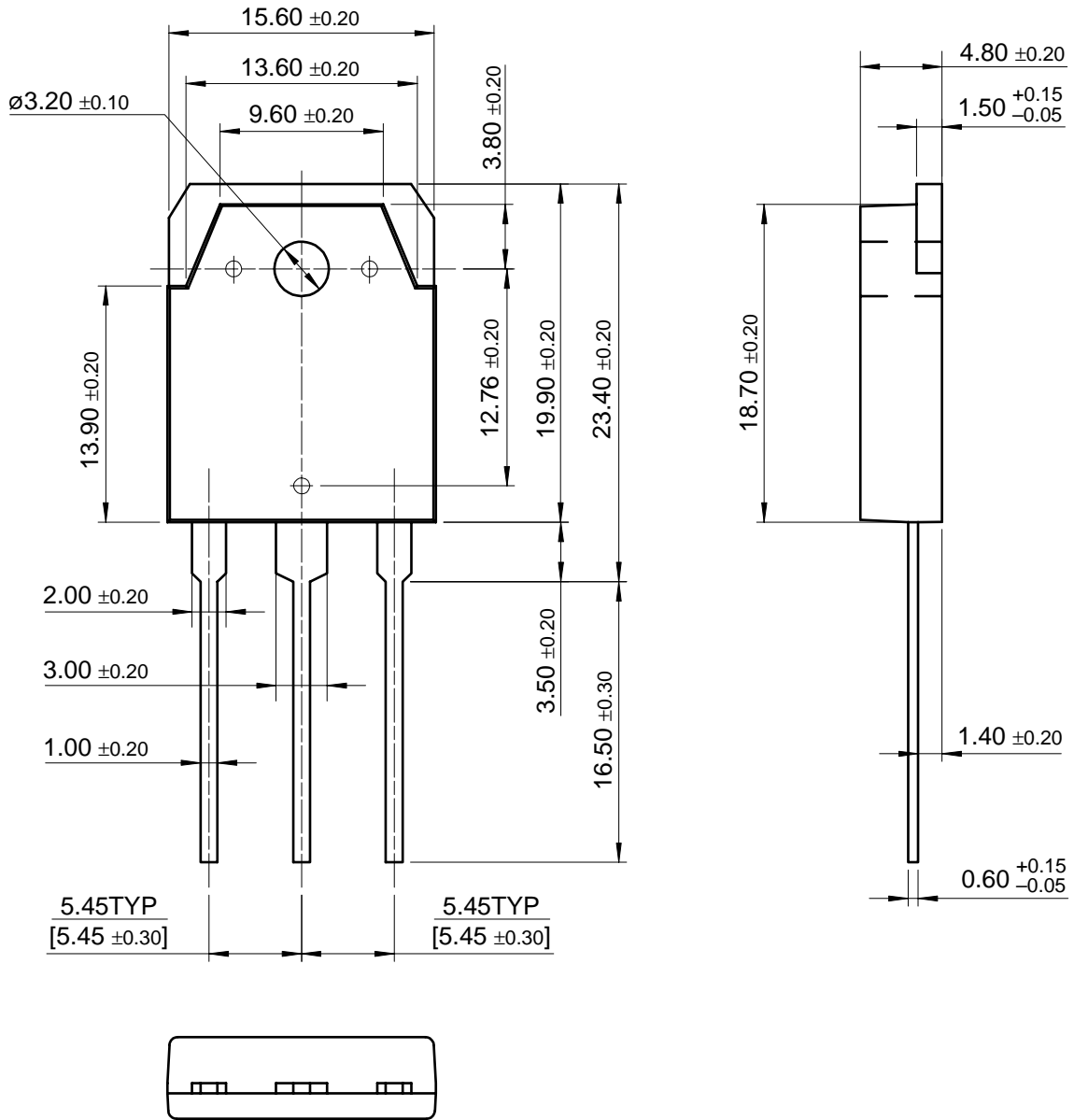


Figure 27. Typical diode forward voltage as a function of junction temperature

TO-3P



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